

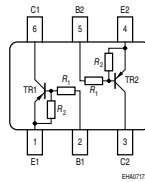
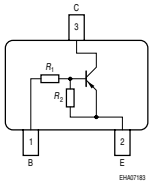
PNP Silicon Digital Transistor

- Switching circuit, inverter, interface circuit, driver circuit
- Built in bias resistor ($R_1 = 47k\Omega$, $R_2 = 47k\Omega$)
- For 6-PIN packages: two (galvanic) internal isolated transistors with good matching in one package



**BCR198/F/L3
BCR198T/W**

**BCR198S
SEMB2**



Type	Marking	Pin Configuration						Package
		1=B	2=E	3=C	-	-	-	
BCR198	WRs	1=B	2=E	3=C	-	-	-	SOT23
BCR198F	WRs	1=B	2=E	3=C	-	-	-	TSFP-3
BCR198L3	WR	1=B	2=E	3=C	-	-	-	TSLP-3-4
BCR198S	WRs	1=E1	2=B1	3=C2	4=E2	5=B2	6=C1	SOT363
BCR198T	WRs	1=B	2=E	3=C	-	-	-	SC75
BCR198W	WRs	1=B	2=E	3=C	-	-	-	SOT323
SEMB2	WR	1=E1	2=B1	3=C2	4=E2	5=B2	6=C1	SOT666

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	50	V
Collector-base voltage	V_{CBO}	50	
Emitter-base voltage	V_{EBO}	10	
Input on voltage	$V_{i(on)}$	50	
Collector current	I_C	70	mA
Total power dissipation- BCR198, $T_S \leq 102^\circ\text{C}$ BCR198F, $T_S \leq 128^\circ\text{C}$ BCR198L3, $T_S \leq 135^\circ\text{C}$ BCR198S, $T_S \leq 115^\circ\text{C}$ BCR198T, $T_S \leq 109^\circ\text{C}$ BCR198W, $T_S \leq 124^\circ\text{C}$ SEMB2, $T_S \leq 75^\circ\text{C}$	P_{tot}	200 250 250 250 250 250 250	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R_{thJS}		K/W
BCR198		≤ 240	
BCR198F		≤ 90	
BCR198L3		≤ 60	
BCR198S		≤ 140	
BCR198T		≤ 165	
BCR198W		≤ 124	
SEMB2		≤ 300	

¹For calculation of R_{thJA} please refer to Application Note Thermal Resistance

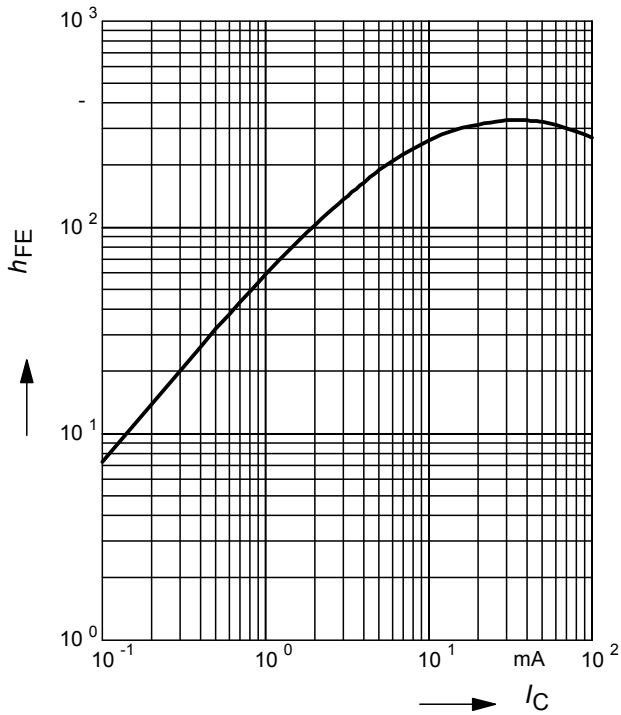
Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage $I_C = 100 \mu\text{A}, I_B = 0$	$V_{(BR)CEO}$	50	-	-	V
Collector-base breakdown voltage $I_C = 10 \mu\text{A}, I_E = 0$	$V_{(BR)CBO}$	50	-	-	
Collector-base cutoff current $V_{CB} = 40 \text{ V}, I_E = 0$	I_{CBO}	-	-	100	nA
Emitter-base cutoff current $V_{EB} = 10 \text{ V}, I_C = 0$	I_{EBO}	-	-	164	μA
DC current gain ¹⁾ $I_C = 5 \text{ V}, V_{CE} = 5 \text{ V}$	h_{FE}	70	-	-	-
Collector-emitter saturation voltage ¹⁾ $I_C = 10 \text{ mA}, I_B = 0,5 \text{ mA}$	V_{CEsat}	-	-	0,3	V
Input off voltage $I_C = 100 \mu\text{A}, V_{CE} = 5 \text{ V}$	$V_{i(off)}$	0,8	-	1,5	
Input on voltage $I_C = 2 \text{ mA}, V_{CE} = 0,3 \text{ V}$	$V_{i(on)}$	1	-	3	
Input resistor	R_1	32	47	62	$\text{k}\Omega$
Resistor ratio	R_1/R_2	0,9	1	1,1	-
AC Characteristics					
Transition frequency $I_C = 10 \text{ mA}, V_{CE} = 5 \text{ V}, f = 100 \text{ MHz}$	f_T	-	190	-	MHz
Collector-base capacitance $V_{CB} = 10 \text{ V}, f = 1 \text{ MHz}$	C_{cb}	-	3	-	pF

¹⁾Pulse test: $t < 300 \mu\text{s}$; $D < 2\%$

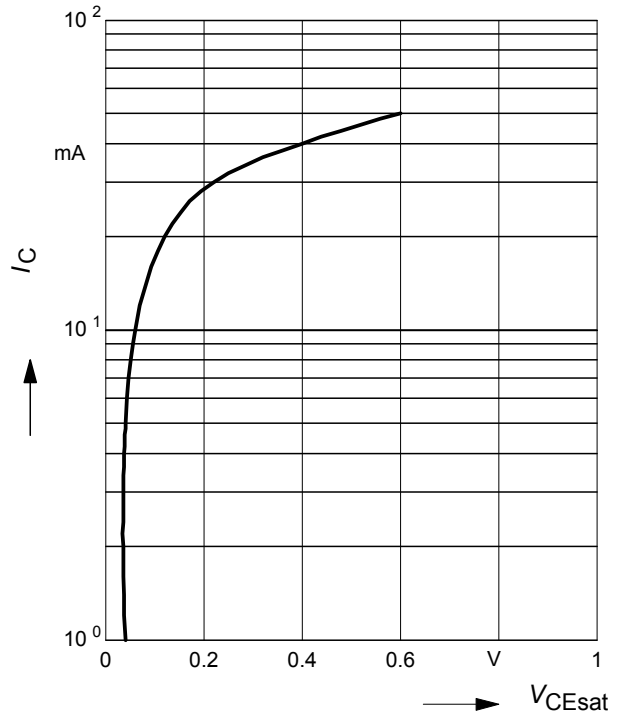
DC current gain $h_{FE} = f(I_C)$

$V_{CE} = 5\text{ V}$ (common emitter configuration)



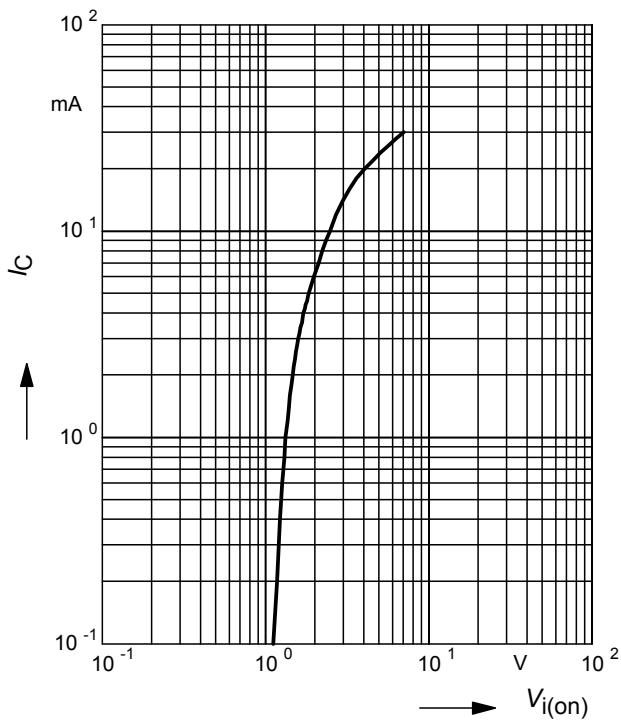
Collector-emitter saturation voltage

$V_{CEsat} = f(I_C), h_{FE} = 20$



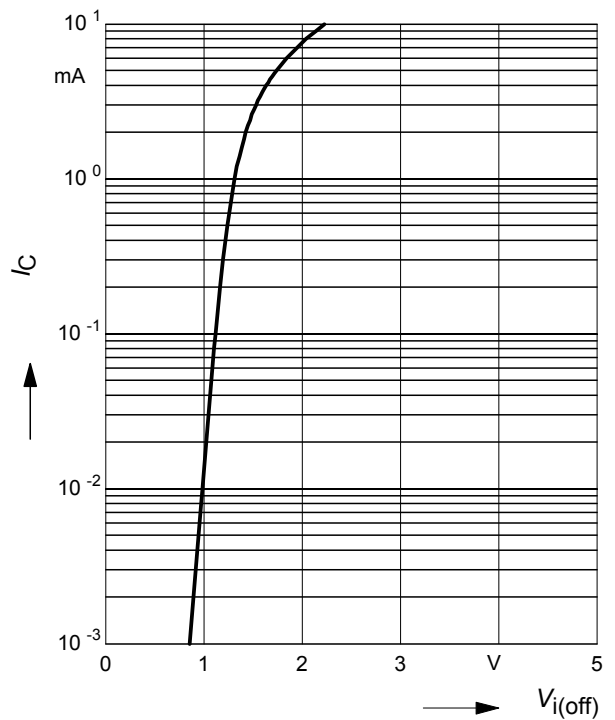
Input on Voltage $V_{i(on)} = f(I_C)$

$V_{CE} = 0.3\text{ V}$ (common emitter configuration)



Input off voltage $V_{i(off)} = f(I_C)$

$V_{CE} = 5\text{ V}$ (common emitter configuration)



Total power dissipation $P_{tot} = f(T_S)$

BCR198



Total power dissipation $P_{tot} = f(T_S)$

BCR198F



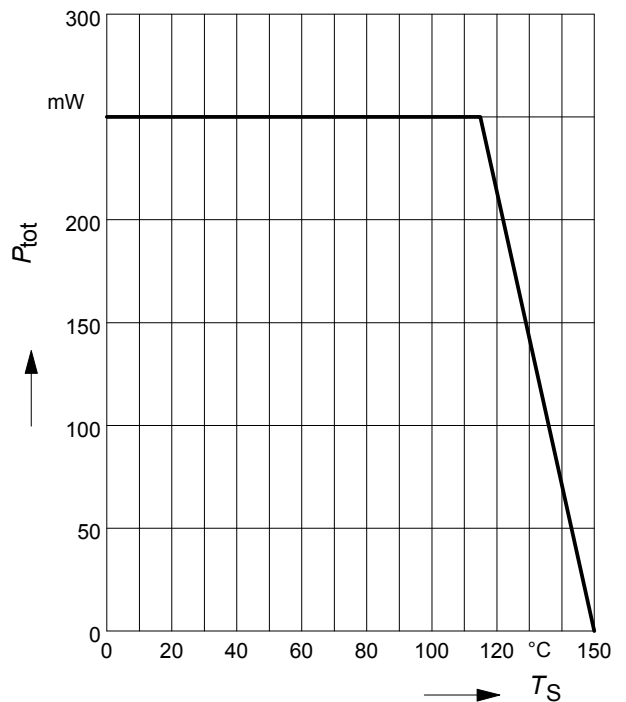
Total power dissipation $P_{tot} = f(T_S)$

BCR198L3



Total power dissipation $P_{tot} = f(T_S)$

BCR198S



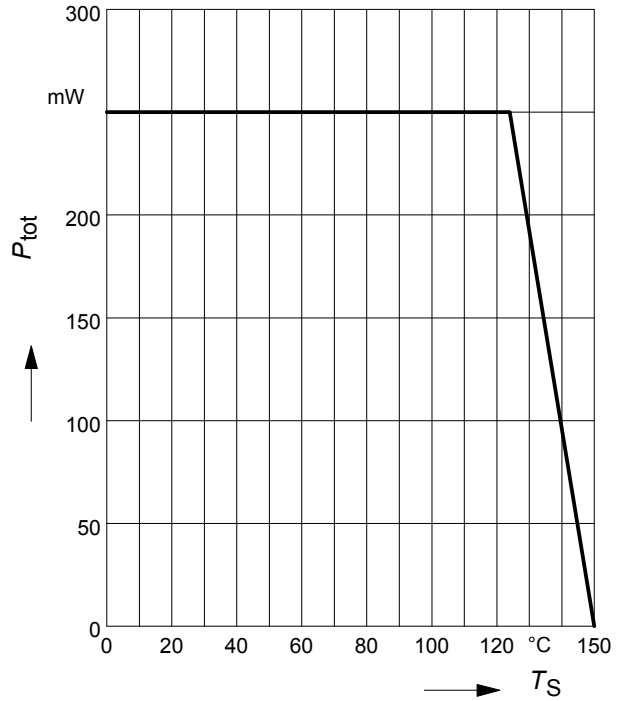
Total power dissipation $P_{tot} = f(T_S)$

BCR198T



Total power dissipation $P_{tot} = f(T_S)$

BCR198W



Total power dissipation $P_{tot} = f(T_S)$

SEMB2



Permissible Pulse Load $R_{thJS} = f(t_p)$

BCR198



Permissible Pulse Load

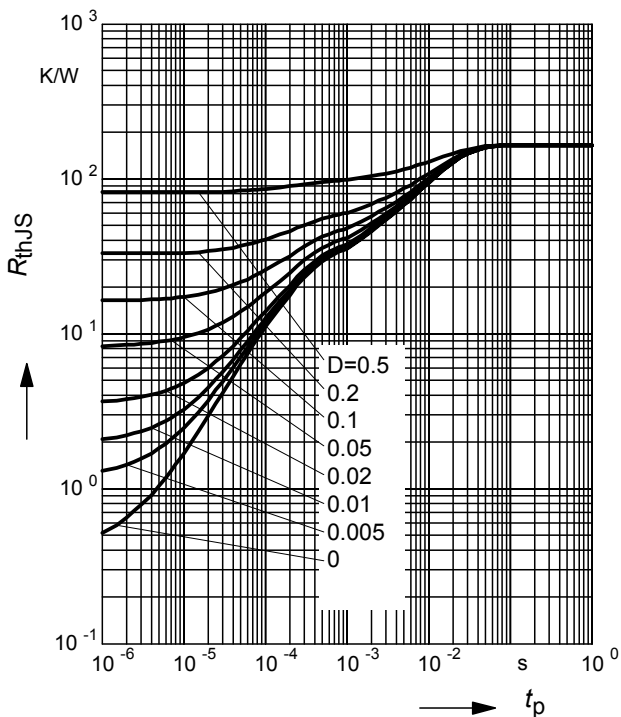
$P_{totmax}/P_{totDC} = f(t_p)$

BCR198



Permissible Puls Load $R_{thJS} = f(t_p)$

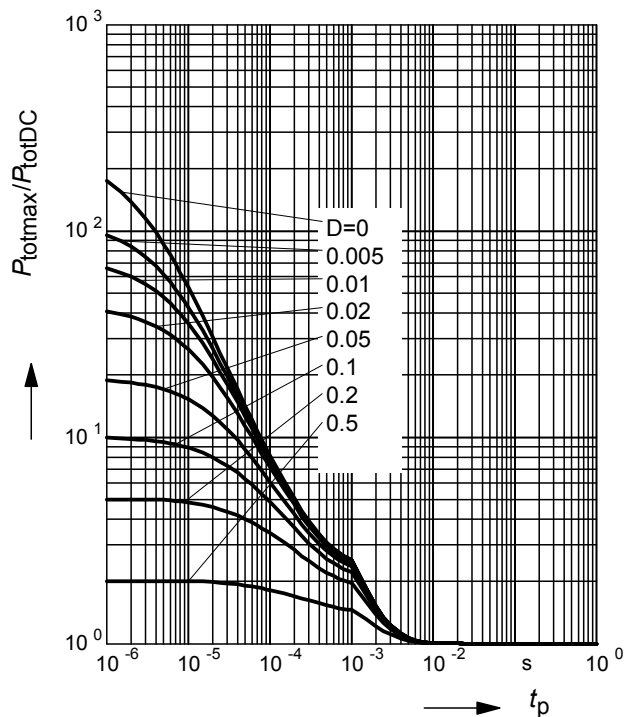
BCR198F



Permissible Pulse Load

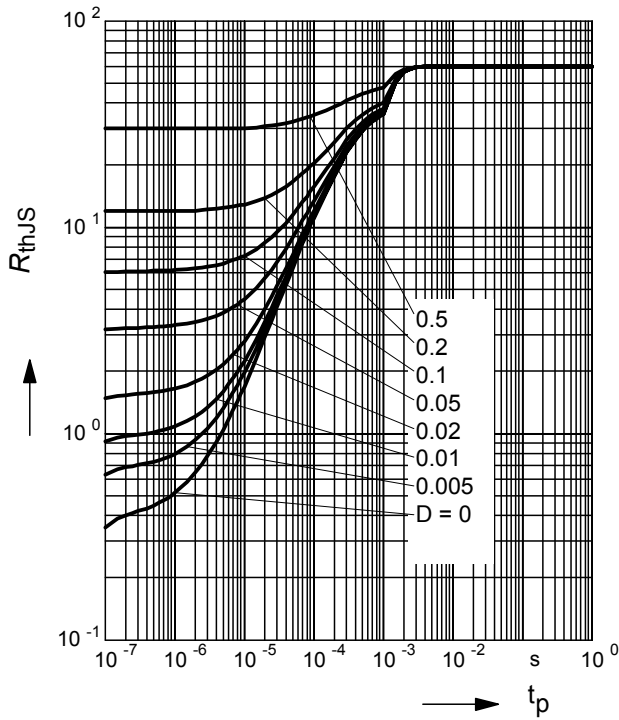
$P_{totmax}/P_{totDC} = f(t_p)$

BCR198F



Permissible Puls Load $R_{thJS} = f(t_p)$

BCR198L3



Permissible Pulse Load

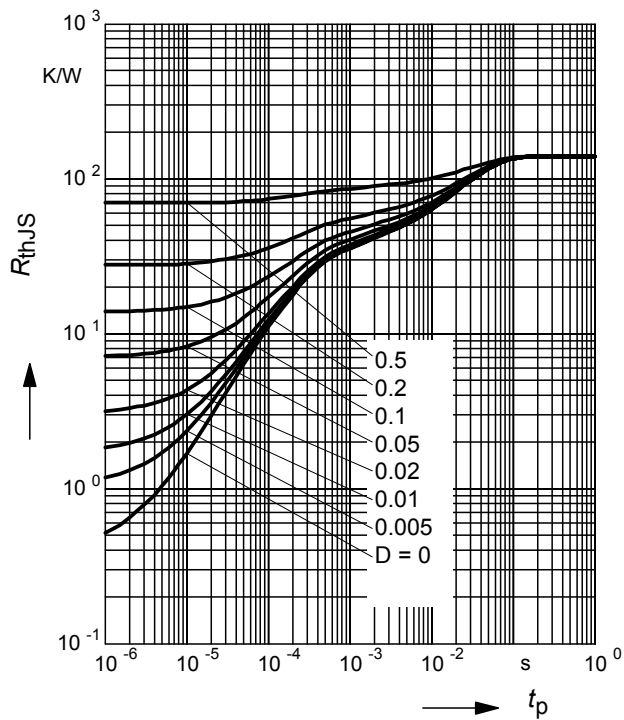
$P_{totmax}/P_{totDC} = f(t_p)$

BCR198L3



Permissible Puls Load $R_{thJS} = f(t_p)$

BCR198S



Permissible Pulse Load

$P_{totmax}/P_{totDC} = f(t_p)$

BCR198S



Permissible Puls Load $R_{thJS} = f(t_p)$

BCR198T



Permissible Pulse Load

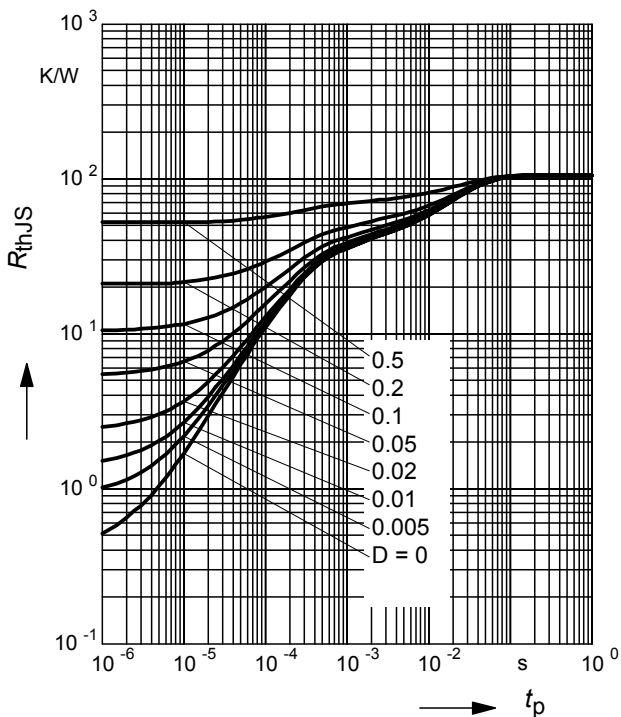
$P_{totmax}/P_{totDC} = f(t_p)$

BCR198T



Permissible Puls Load $R_{thJS} = f(t_p)$

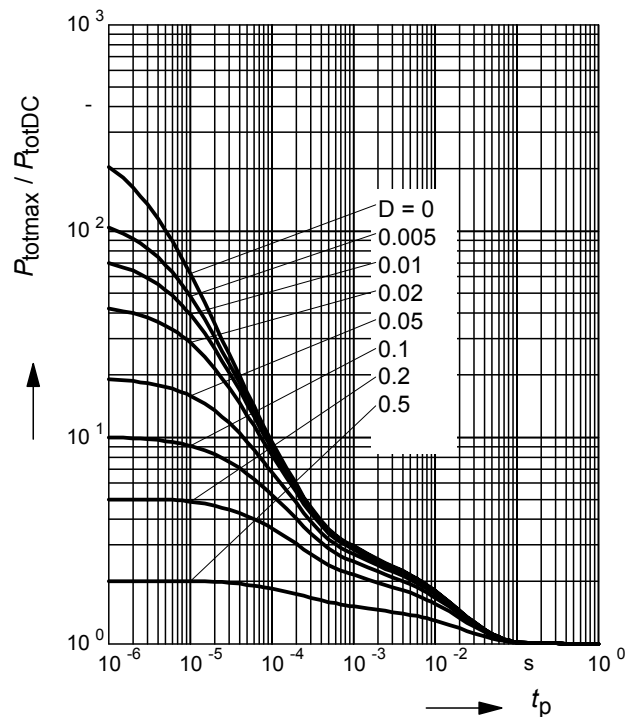
BCR133W



Permissible Pulse Load

$P_{totmax}/P_{totDC} = f(t_p)$

BCR198W



Permissible Puls Load $R_{thJS} = f(t_p)$

SEMB2



Permissible Pulse Load

$P_{totmax}/P_{totDC} = f(t_p)$

SEMB2



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